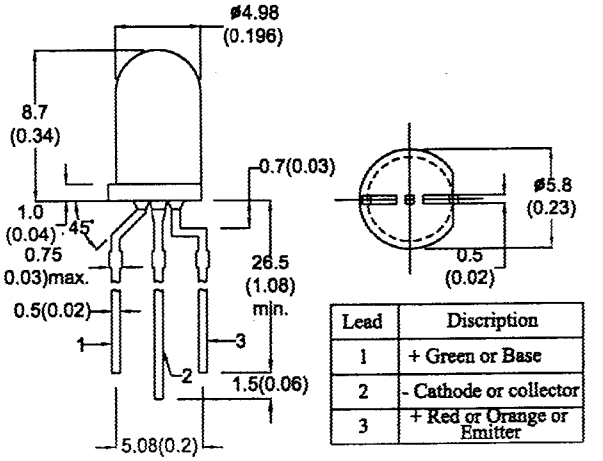
MICRO ELECTRONICS

HIGH EFFICIENCY RED/GREEN BI-COLOR LAMP

DESCRIPTION

A high efficiency red and green bi-color lamp made of GaAsP, GaP LED chip offering a changing color characteristics. These two light emitting diodes are mounted in 5mm diameter transparent lens.



Lead	Discription
1	+ Green or Base
2	- Cathode or collector
3	+ Red or Orange or Emitter

- All dimension in mm(inch)
- No Scale
- Tol. : +/-0.3mm

ABSOLUTE MAXIMUM RATINGS

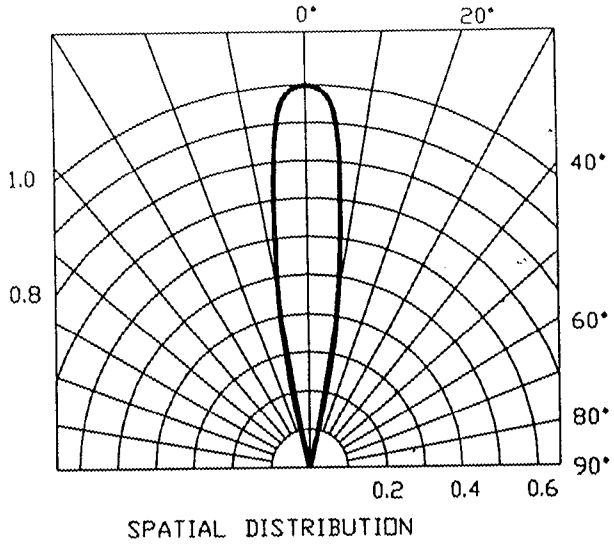
	High efficiency Red	Green
Power Dissipation @ Ta=25°C	100mW	100mW
Forward Current, DC (IF)	30mA	30mA
Reverse Voltage	5V	5V
Operating & Storage Temperature Range	-55 to +100°C	
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.	

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

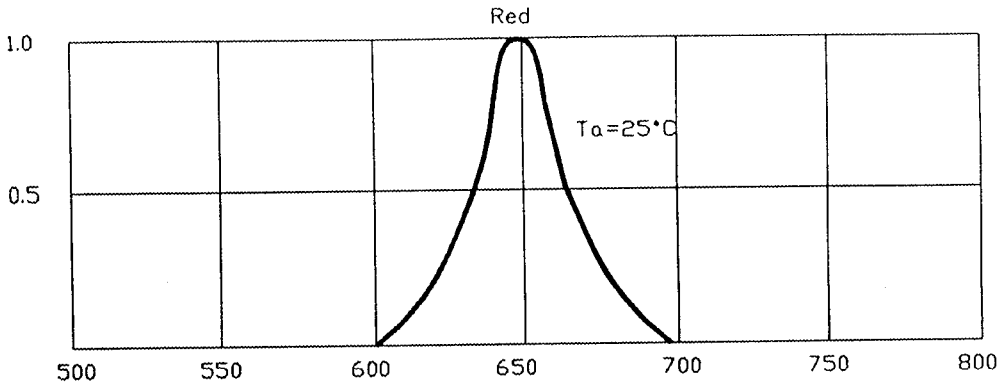
PARAMETER		SYMBOL	RED	GREEN	UNIT	CONDITIONS
Forward Voltage	MAX	VF	3.0	3.0	V	IF=20mA
Reverse Breakdown Voltage	MIN	BVR	5	5	V	IR=100μA
Luminous Intensity	MIN	IV	50	70	mcd	IF=20mA
	TYP		100	120	mcd	IF=20mA
Peak Wavelength	TYP	λp	650	570	nm	IF=20mA
Spectral Line Half Width	TYP	Δλ	30	30	nm	IF=20mA

MICRO ELECTRONICS LTD.
38, Hung To Road, Microtron Bulding, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5

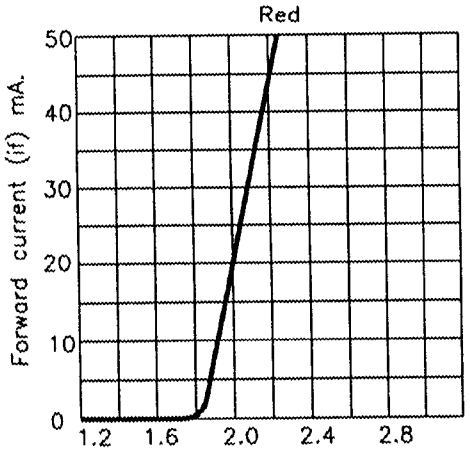
MSGB51T(RED)



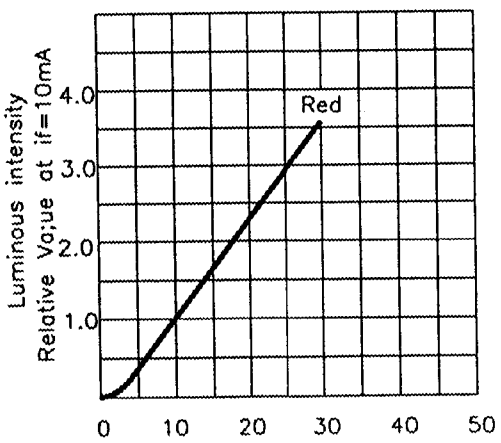
SPATIAL DISTRIBUTION



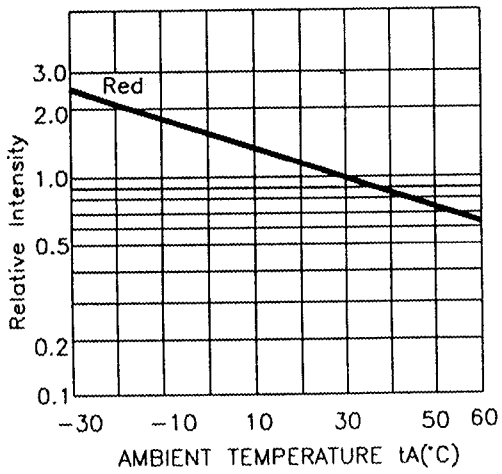
RELATIVE INTENSITY VS.WAVELENGTH



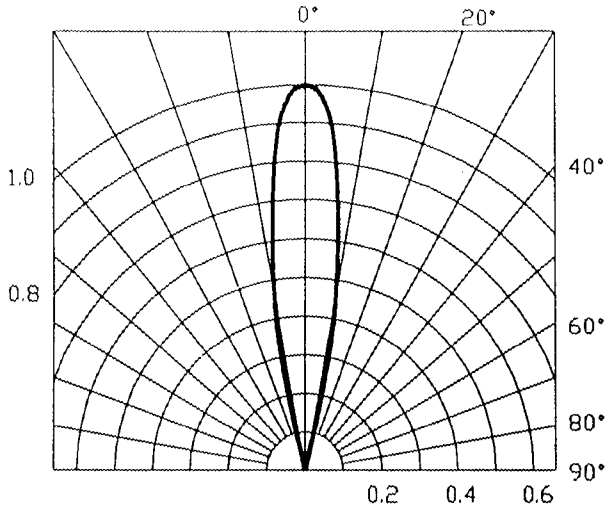
FORWARD CURRENTS VS.. FORWARD VOLTAGE



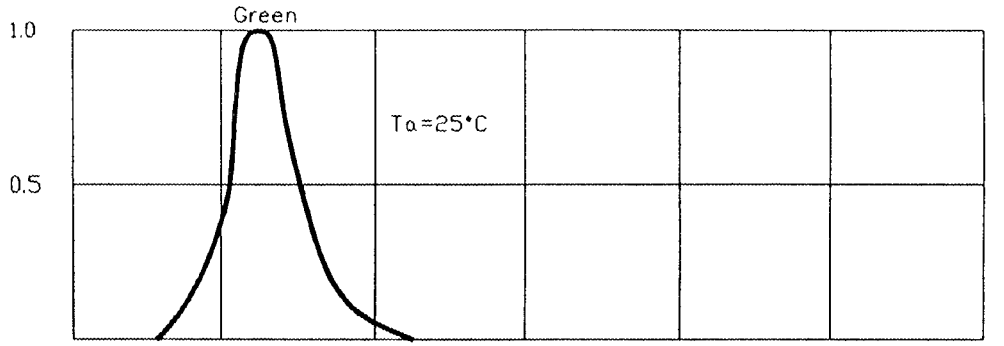
RELATIVE LUMINOUS INTENSITY VS. FORWARD CURRENT



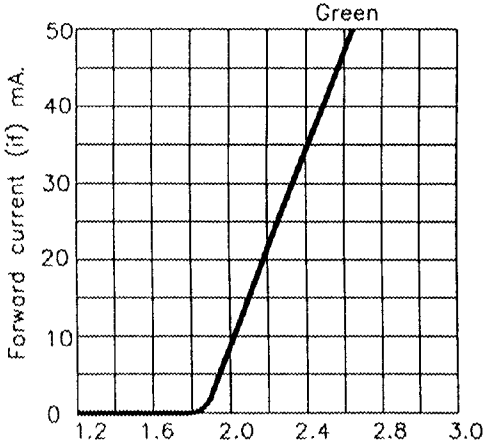
MSGB51T(GREEN)



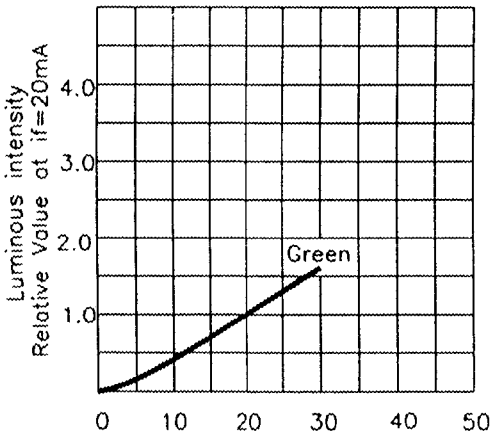
SPATIAL DISTRIBUTION



RELATIVE INTENSITY VS.WAVELENGTH



FORWARD CURRENTS VS.. FORWARD VOLTAGE



RELATIVE LUMINOUS INTENSITY VS. FORWARD CURRENT

